

Abstracts

RF Characteristics of P-Well GaAs MESFETs

P.C. Canfield and D.J. Allstot. "RF Characteristics of P-Well GaAs MESFETs." 1990 MTT-S International Microwave Symposium Digest 90.3 (1990 Vol. III [MWSYM]): 1077-1080.

The first experimental results on the RF performance of p-well MESFETs are presented. It is shown that the small-signal equivalent circuit for the p-well MESFET must include a series RC branch between the source and drain to properly model the undepleted well and its contact. The dependence of the equivalent circuit parameter values on the doping of the p-well is presented and shown to have only a minor effect on the RF performance.

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